



### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
60V	68mΩ @ V <sub>GS</sub> = 10V	8.5A	
00 V	100mΩ @ V <sub>GS</sub> = 4.5V	7.0A	

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor Control
- · Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

## **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

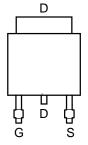
### **Mechanical Data**

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (Approximate)

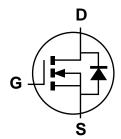




Top View



Pin Out—Top View



**Equivalent Circuit** 

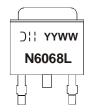
## Ordering Information (Note 5)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMN6068LK3Q-13	N6068L	13	16	2500

Note:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Oll = Manufacturer's Marking
N6068L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01-52)



### Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage		(Note 6)	$V_{GS}$	±20	V
Single Pulsed Avalanche En	ergy	(Note 12)	E <sub>AS</sub>	37.5	mJ
Single Pulsed Avalanche Current (No		(Note 12)	I <sub>AS</sub>	5.0	A
		(Note 8)		8.5	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = 70^{\circ}C$ (Note 8)	$I_{D}$	6.8	Α
		(Note 7)		6.0	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 9)	$I_{DM}$	22.2	Α
Continuous Source Current (Body Diode) (Note 8)		(Note 8)	Is	10.2	Α
Pulsed Source Current (Body Diode) (Note 9)		(Note 9)	I <sub>SM</sub>	22.2	A

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

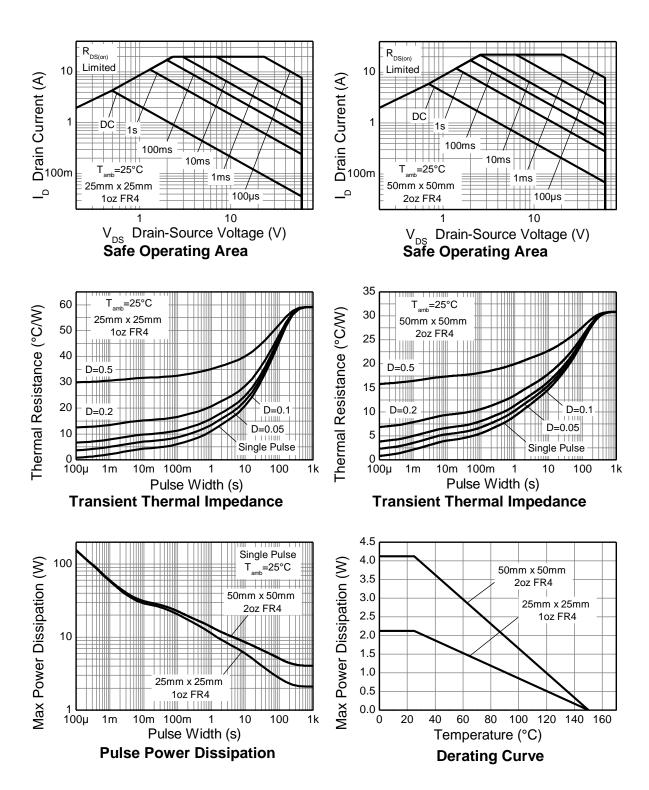
Characteristic		Symbol	Value	Unit	
	(Note 7)		4.12 33		
Power Dissipation Linear Derating Factor	(Note 8)	P <sub>D</sub>	8.49 67.9	W mW/°C	
	(Note 10)		2.12 16.9		
Thermal Resistance, Junction to Ambient	(Note 7) (Note 8)	R <sub>eJA</sub>	30.3 14.7		
,	(Note 10)		59.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 11)	R <sub>OJL</sub>	3.09		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes:

- 6. AEC-Q101  $V_{GS}$  maximum is ±16V.
- 7. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single-sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 8. Same as note 2 except the device is measured at  $t \le 10$  sec.
- 9. Same as note 2 except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.
- 10. For a device surface mounted on 25mm × 25mm × 1.6mm FR4 PCB with high coverage of single-sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 11. Thermal resistance from junction to solder-point (at the end of the drain lead).
- 12. UIS in production with L = 3.0mH,  $I_{AS}$  = 5.0A,  $R_{G}$  = 25 $\Omega$ ,  $V_{DD}$  = 50V, starting  $T_{J}$  = 25 $^{\circ}C$



## **Thermal Characteristics**





## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

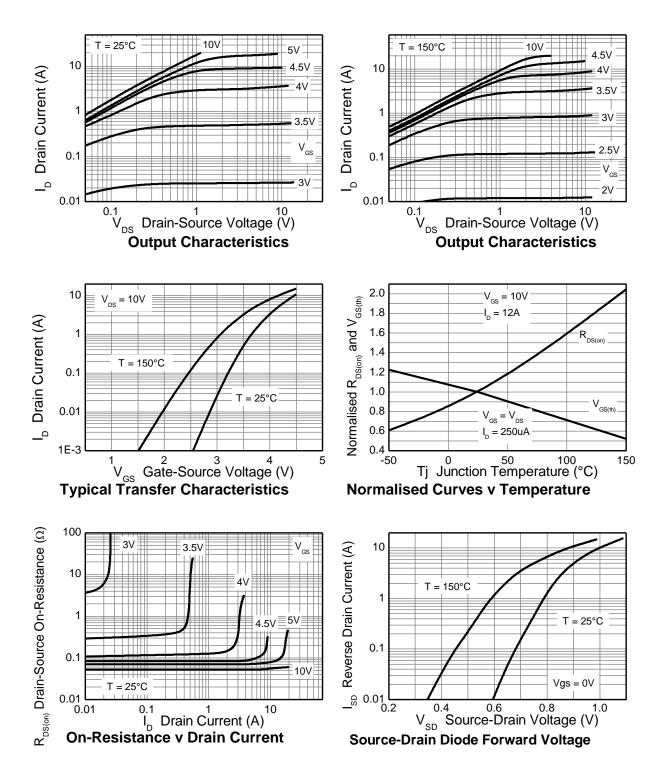
Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ondition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	0.5	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> =	0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub>	= 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	_	3.0	V	I <sub>D</sub> = 250μA, V <sub>DS</sub> =	· V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 13)	D			0.068	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12	2A
Static Drain-Source Off-Resistance (Note 13)	R <sub>DS (ON)</sub>	_		0.100	22	$V_{GS} = 4.5V, I_{D} = 6$	6A
Forward Transconductance (Notes 13 & 14)	<b>g</b> fs	_	19.7		S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12	2A
Diode Forward Voltage (Note 13)	$V_{SD}$	_	0.98	1.15	V	I <sub>S</sub> = 12A, V <sub>GS</sub> = 0	V
Reverse recovery time (Note 14)	t <sub>rr</sub>		145	_	ns	I <sub>S</sub> = 12A, di/dt= 100A/μs	
Reverse recovery charge (Note 14)	Q <sub>rr</sub>	_	929	_	nC		
DYNAMIC CHARACTERISTICS (Note 14)							
Input Capacitance	$C_{iss}$	_	502	_	pF		01/
Output Capacitance	Coss	_	45.7	_	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V -f= 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	27.1	_	pF	1- 11/11/12	
Total Gate Charge	Qg	_	5.55	_	nC	V <sub>GS</sub> = 4.5V	
Total Gate Charge	$Q_g$	_	10.3	_	nC		V <sub>DS</sub> = 30V
Gate-Source Charge	$Q_{gs}$	_	1.6	_	nC	V <sub>GS</sub> = 10V I <sub>D</sub> = 12A	
Gate-Drain Charge	$Q_{gd}$	_	3.5	_	nC		
Turn-On Delay Time (Note 15)	t <sub>D(on)</sub>	_	3.6	_	ns	$V_{DD} = 30V, \ V_{GS} = 10V$ $I_{D} = 12A, \ R_{G} \cong 6.0\Omega$	
Turn-On Rise Time (Note 15)	t <sub>r</sub>	_	10.8	_	ns		
Turn-Off Delay Time (Note 15)	t <sub>D(off)</sub>	_	11.9	—	ns		
Turn-Off Fall Time (Note 15)	t <sub>f</sub>	_	8.7	_	ns		

Notes:

<sup>13.</sup> Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2% 14. For design aid only, not subject to production testing. 15. Switching characteristics are independent of operating junction temperatures.

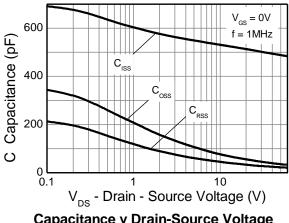


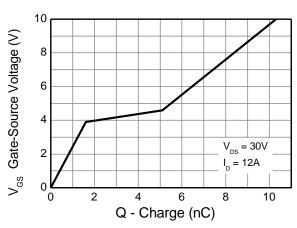
## **Typical Characteristics**





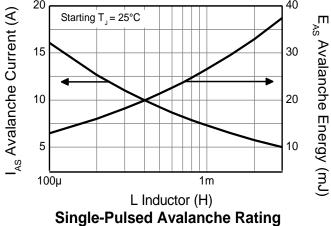
# Typical Characteristics (Continued)





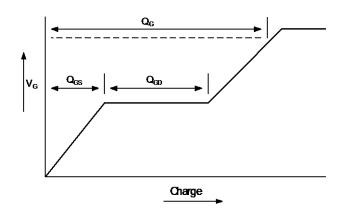
Capacitance v Drain-Source Voltage

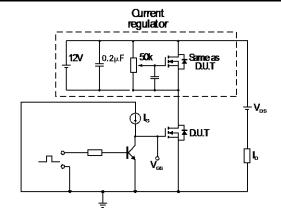
**Gate-Source Voltage v Gate Charge** 





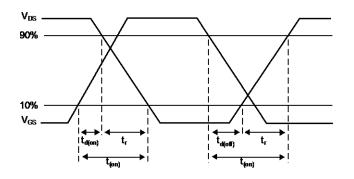
## **Test Circuits**

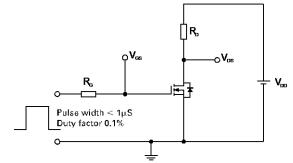




Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

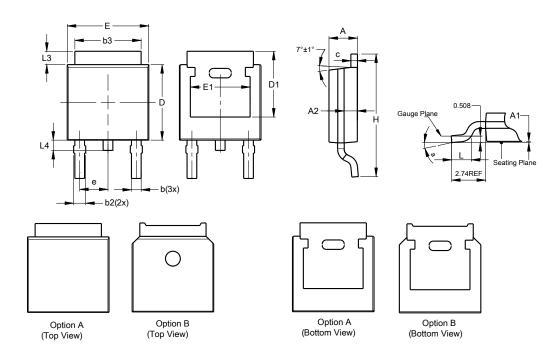
Switching time test circuit



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (Standard)

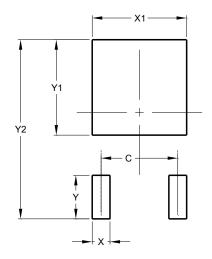


TO252 (Standard)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.60	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (Standard)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10 700



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